TOSHIBA Transistor Silicon PNP Triple Diffused Type

2SA2121

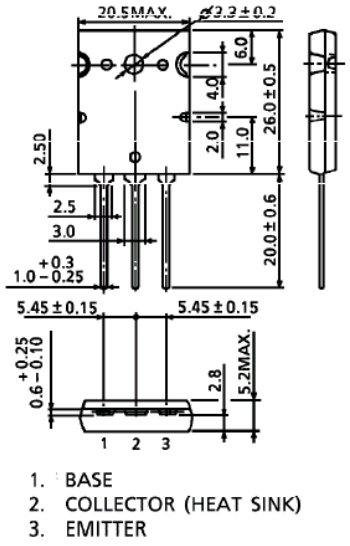
Power Amplifier Applications

- P_C = 220W
- Complementary to 2SC5949

Maximum Ratings (Tc = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	−200	V
Collector-emitter voltage	V_{CEO}	−200	V
Emitter-base voltage	V_{EBO}	−5	V
Collector current	I_C	−15	A
Base current	I_B	−1.5	A
Collector power dissipation	P_C	220	W
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	−55 to 150	°C

Unit: mm



JEDEC	—
JEITA	—
TOSHIBA	2-21F1A

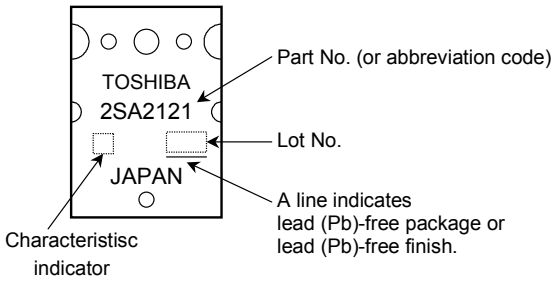
Weight: 9.75 g (typ.)

Electrical Characteristics (Tc = 25°C)

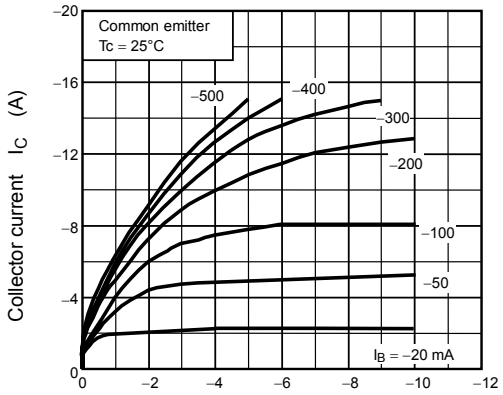
Characteristic	Symbol	Test Conditions	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = −200 V, I_E = 0	—	—	−5.0	μA
Emitter cut-off current	I_{EBO}	V_{EB} = −5 V, I_C = 0	—	—	−5.0	μA
Collector-emitter breakdown voltage	$V_{(BR)\ CEO}$	I_C = −50 mA, I_B = 0	−200	—	—	V
DC current gain	$h_{FE\ (1)}$ (Note 1)	V_{CE} = −5 V, I_C = −1 A	55	—	160	
	$h_{FE\ (2)}$	V_{CE} = −5 V, I_C = −8 A	35	60	—	
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	I_C = −10 A, I_B = −1 A	—	−1.5	−3.0	V
Base-emitter voltage	V_{BE}	V_{CE} = −5 V, I_C = −8 A	—	−1.0	−1.5	V
Transition frequency	f_T	V_{CE} = −5 V, I_C = −1 A	—	25	—	MHz
Collector output capacitance	C_{ob}	V_{CB} = −10 V, I_E = 0, f = 1 MHz	—	470	—	pF

Note 1: $h_{FE(1)}$ classification R: 55 to 110, O: 80 to 160

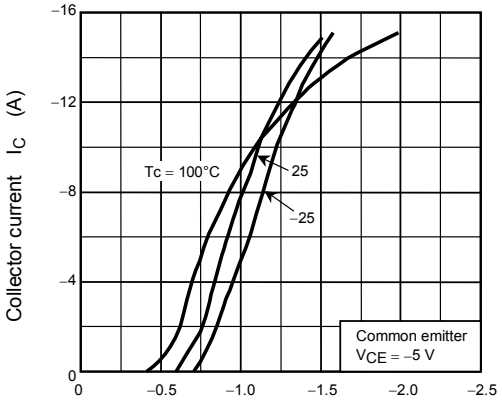
Marking



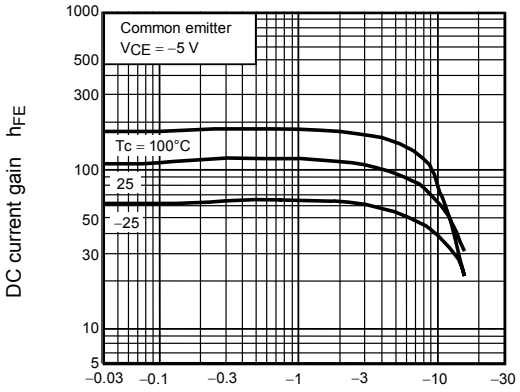
$I_C - V_{CE}$



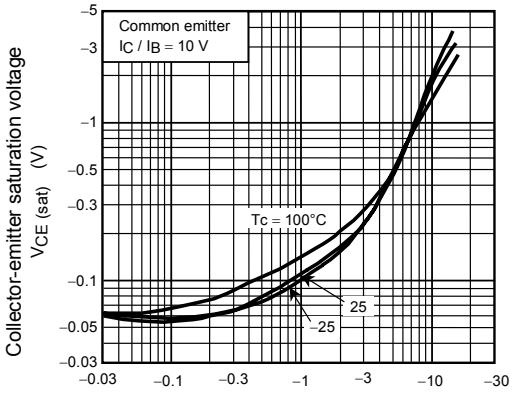
$I_C - V_{BE}$



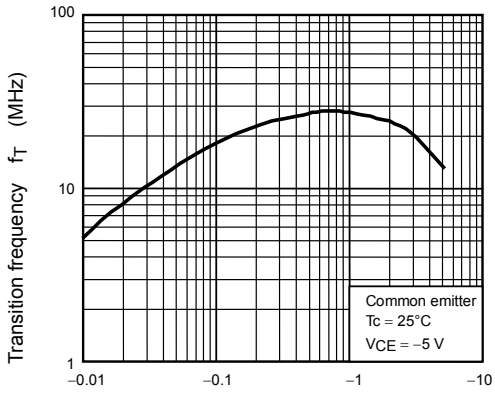
$h_{FE} - I_C$



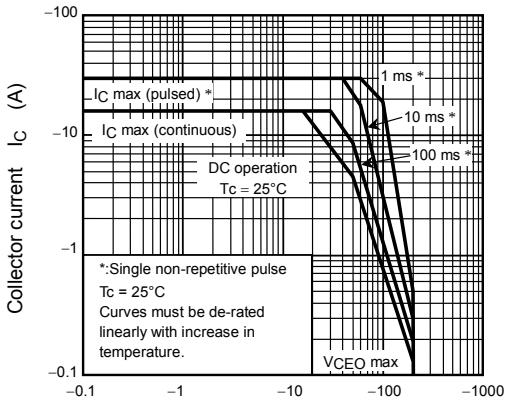
$V_{CE\ (sat)} - I_C$



$f_T - I_C$



Safe Operating Area



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